

# Flash Memory Summit 2018 MRAM Update

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## Four Generations of Production MRAM



Not Scalable beyond 130nm (write power) Not Scalable beyond 65/40 nm (retention) Fully scalable Endurance-Retention-Speed tradeoff → Limited persistence and/or endurance and/or speed

> 256Mbit at threshold of mass production

Embedded NVM on threshold of production in 22-28nm CMOS Infinite endurance + high intrinsic speed

Fully scalable

= persistent RAM compatible

SOT solves STT shortfalls for RAM applications

# Manufacturing Ramp at Foundries

- Flash Memory Summit
  Samsung, TSMC, Global Foundries in ramp up in 22-28nm insertions
  - In logic processes as 'embedded memory' in SOC
  - STT-MRAM introduction primarily as 'roadmap substitution' for embedded NOR Flash replacement
    - Plus some use as 'pseudo' RAM
      - Compromises on speed, endurance, retention
    - Production starts 2018-2019
  - STT-MRAM not applicable as general purpose embedded SRAM replacement



# **Production Equipment Availability**

- Essential 300mm tools with suitable wafer throughput and technical capability reaching availability
  - Applied Materials, TEL, Canon/Anelva
  - Magnetic film deposition and etch are principle requirements
- Yield and other process control converging on manufacturable, but not yet equal to incumbent memory types



## **Discrete MRAM in Storage** 'The Low Hanging Fruit'

#### **RAID** systems

5-10+ memories per RAID system controller \$100-1000 per system 5M+ units/year



#### **SSD / HDD controller**

R/W cache, Logical/Physical Address Table, etc... in mission critical high performance \$1-4 per drive SDD \$50-100 per system in high end storage system 1-2 memories per drive 500M+ units per year \$10-20 per drive



### "Front End" multi-Gb buffer

150M units per year



### Critical mission: 'Protect Data in Flight'

Requires: Speed and Endurance of DRAM, with instantaneous power-off data retention

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### 'High Impact' MRAM Application Promise Top 10 List

- 1. >1 Million IOP SSD
- 2. Unified Memory (XIP) Microcontroller
- 3. Persistent Cache for Mobile CPU
- 4. Big-Capacitor-Free Performance SSD
- 5. SOC Embedded SRAM Replacement
- 6. SOC Embedded Flash Replacement
- 7. 'High Training Rate/Low Training Energy' NVM Memory for AI
- 8. Persistent Cache for Storage System
- 9. Rad Hard High Density Flash Replacement
- 10. 'High Endurance' Flash Gap



### 'High Impact' MRAM Application Promise Top 10 List – Near Term Impact Predictions

- 1. >1 Million IOP SSD
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